Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (currently amended) A method of growing a metal oxide film on a substrate by atomic layer deposition comprising:

(i) introducing separate pulses of metal alkyl amide and ozone into a reaction chamber containing a substrate, wherein said metal is a Group 4 metal Hf, Zr, Ti; and

(ii) repeating step (i) until a film of a target thickness is achieved,

where the metal alkyl amide has the formula $M(NR^1R^2)_4$, wherein M represents a Group 4 metal, R^1 is an ethyl unit, and R^2 is a methyl unit.

2. (original) The method of claim 1, wherein the metal oxide is hafnium oxide.

3. (cancelled).

4. (original) The method of claim 1 wherein the substrate is silicon.

5. (currently amended) A method of forming a gate insulator for a transistor comprising:

(i) growing a metal oxide mono layer on a substrate by atomic layer deposition by introducing separate pulses of a metal alkyl amide and ozone into a reaction chamber containing a substrate, wherein said metal is a Group 4 metal;

(ii) repeating step (i) until a dielectric film of a target thickness is achieved; and

(iii) positioning a conductive layer over the dielectric layer,

where the metal alkyl amide has the formula $M(NR^1R^2)_4$, wherein M represents a Group 4 metal, R^1 is an ethyl unit, and R^2 is a methyl unit.

6. (original) The method of claim 5, wherein the metal oxides are hafnium oxide, zirconium oxide and titanium oxide.

7. (canceled)

8. (original) The method of claim 5 wherein the substrate is silicon.

9. (currently amended) A method of forming a capacitor comprising:

(i) forming a metal oxide mono layer by atomic layer deposition by introducing separate pulses of a metal alkyl amide precursor and ozone into a reaction chamber containing a substrate, wherein said metal is a Group 4 metal;

(ii) repeating step (i) until a film of a target thickness is achieved; and

(iii) positioning said film between two electrodes,

where the metal alkyl amide has the formula $M(NR^1R^2)_4$, wherein M represents a Group 4 metal, R^1 is an ethyl unit, and R^2 is a methyl unit.

10. (original) The method of claim 9, wherein the metal oxides are hafnium oxide, ZrO_2, and TiO_2.

11. (canceled)

12. (original) The method of claim 9, wherein the substrate is one of the two electrodes.